



Data Sheet

N-channel 40 V, 29 mΩ logic level MOSFET in LFPAK56

Manufacturers NXP Semiconductor

Package/Case LFPAK56Power-SO8

Product Type Transistors

RoHS

Lifecycle



Images are for reference only

Please submit RFQ for BUK9Y29-40E or Email to us; sales@ovaga.com We will contact you in 12 hours.

RFO

General Description

BUK9Y29-40E is a specific part number for a N-channel MOSFET transistor manufactured by Nexperia. This MOSFET has a Vds (drainsource voltage) of 40V, a continuous drain current (Id) of 24A, and a low on-resistance of 9.5 mOhm.

Features

Low on-resistance (9.5 mOhm) for low power dissipation and Power management and conversion in server and telecom systems high efficiency

High continuous drain current (24A) for power handling capability

High-speed switching for efficient power management

Avalanche energy rated for improved reliability in rugged environments

Low gate charge for easy drive of the MOSFET

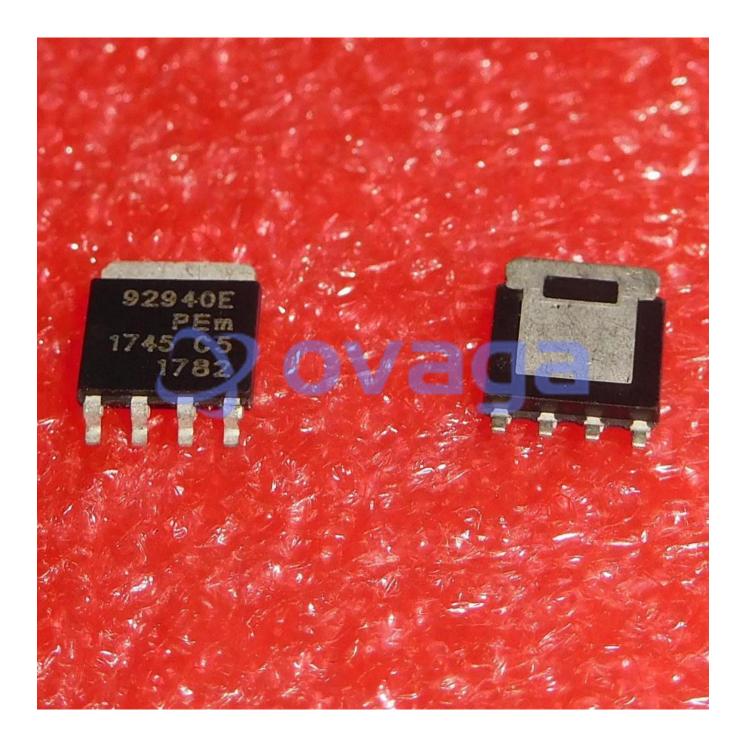
Application

Power supplies in consumer electronics and lighting

Motor control in industrial automation and robotics

Automotive applications like electric power steering, transmission control, and engine management

LED lighting drivers





Related Products



BUK9Y21-40E

NXP Semiconductor LFPAK56Power-SO8



BUK9212-55B

NXP Semiconductor TO-428



BUK9K18-40E

NXP Semiconductor SOP-8



BUK98150-55A

NXP Semiconductor

SOT223



BUK7K25-40E

NXP Semiconductor
Dual



BUK9Y22-100E

NXP Semiconductor LFPAK56Power-SO8



BUK9K6R2-40E

NXP Semiconductor LFPAK56D



BUK9Y12-40E

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LFPAK56Power-SO8